

LAB

What's new v5.8

What's New LAB 5.8



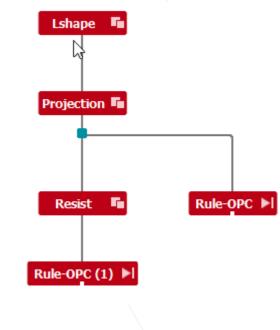
Rule OPC



Rule OPC Enhancement

Defined rules can be previewed and optimized in Rule-OPC panel.

- Rule-OPC module has to be connected to an executed exposure module or resist module. The connection to an exposure or resist module is required to get all needed parameter for the simulation.
- The preview functionallity allows the user to get a quick and easy impression of the impact by the defined rules on the used layout.
- The optimizer functionally goes one step further and optimizes defined parameters in rules, to allow an easier setup of rule sets.





Rule Definition Preview

The preview functionality shows:

- Segment assignment on original layout
- Resulting layout after rule application
- Exposure simulation result of corrected layout

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OPC Rule Optimization

Define the parameter range in the rules, using the following format:

%[min value:max value]%

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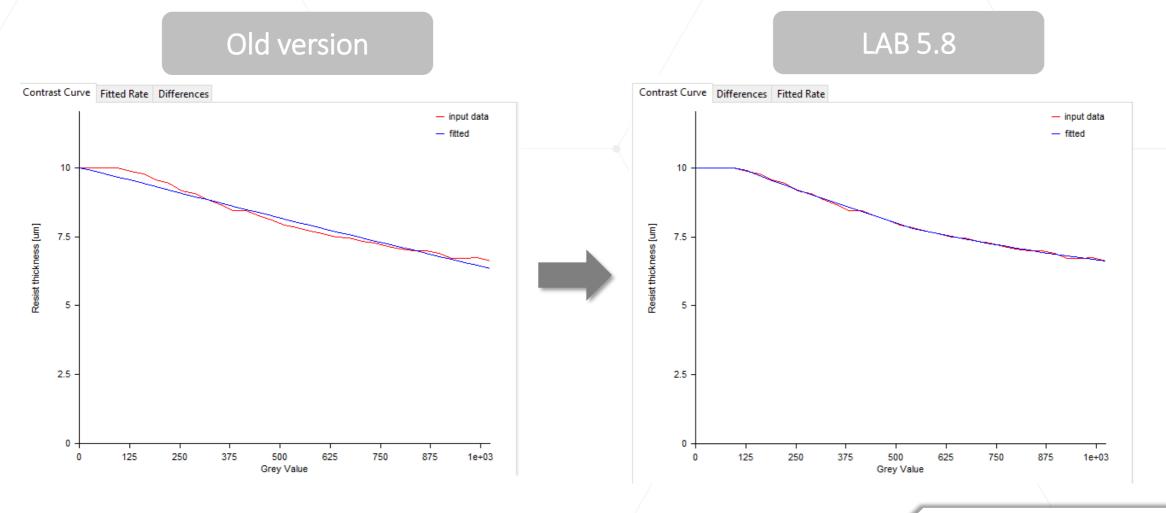


Contrast Curve Fitting



Segmented Development Rate Model

The old development rate model has been replaced with a new segmentwise developmet rate model, to ensure better fitting results for contrast curves.





Tool Spectrum

The user can now select the used exposure spectrum to ensure better fitting of the Contrast Curve.

Add Material			×
Name AZ1518 Type Resist			
Exposure Type			
Proximity OProjection OLaser OE-Beam			
Optical Development Etching Comments			
AZ351B <add></add>			
Developer main settings			
Rename developer	Tool Spectrum X	Delete developer	
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Usability



Recent Flow List

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Maximum Polygon Vertices [512 - 6553	5] 8192 ~		
Curve Approximation Accuracy [um]	0.001000		
Parallel Processing of Loops			
Warning on Module Reset			
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License Manage			
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Hand module license back after exec			
License Server http://localhost:223	50/Server.html		
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File menu keeps up to 6 🚔 flow p	ath entries.		
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• The number of recent flows can be adjusted via a properties setting.

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Thank You!

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Pro **SEM**

VIEWER

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